

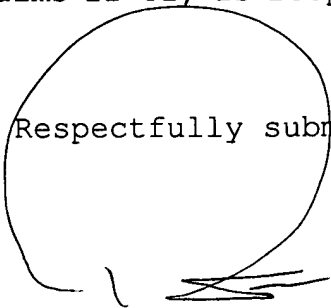
**REMARKS**

Applicants hereby elect with traverse the prosecution of Group I, method claims 1-21. Non-elected claims 22-32 have been withdrawn from further consideration by the Examiner. The restriction requirement is further respectfully traversed for the following reasons. While the Examiner contended that "in the instant case, the product can be made by using a doped glass for the dopant source to form doped regions", the Applicants respectfully submit such process steps would not be possible in the present invention method for arriving at the structure recited in claim 22. To enable the structure recited in claim 22, the last two steps recited in claim 1 must be performed, i.e. etching back the spacer dielectric layer to be an unetched spacer dielectric layer portion overlying the first doped region while forming a sidewall spacer of a predetermined width overlying a first portion of the second doped region; and, carrying out a second ion implantation process to form a relatively higher dopant concentration in a second portion of the second doped region".

U.S.S.N. 10/723,072

The restriction requirement is therefore respectfully traversed. The examination of Group I, claims 1-21, together with the examination of Group II claims 22-32, is respectfully requested of the Examiner.

Respectfully submitted,



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